

Plastic Medium-Power Complementary Silicon Transistors

... designed for general-purpose amplifier and low-speed switching applications.

- High DC Current Gain —
 $h_{FE} = 2500$ (Typ) @ $I_C = 4.0$ Adc
- Collector Emitter Sustaining Voltage — @ 100 mAdc
 $V_{CEO(sus)} = 80$ Vdc (Min) — BDX53B, 54B
 $= 100$ Vdc (Min) — BDX53C, 54C
- Low Collector-Emitter Saturation Voltage —
 $V_{CE(sat)} = 2.0$ Vdc (Max) @ $I_C = 3.0$ Adc
 $= 4.0$ Vdc (Max) @ $I_C = 5.0$ Adc
- Monolithic Construction with Built-In Base-Emitter Shunt Resistors
- TO-220AB Compact Package

MAXIMUM RATINGS

Rating	Symbol	BDX53B BDX54B	BDX53C BDX54C	Unit
Collector-Emitter Voltage	V_{CEO}	80	100	Vdc
Collector-Base Voltage	V_{CB}	80	100	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous Peak	I_C	8.0 12		Adc
Base Current	I_B	0.2		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	60 0.48		Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

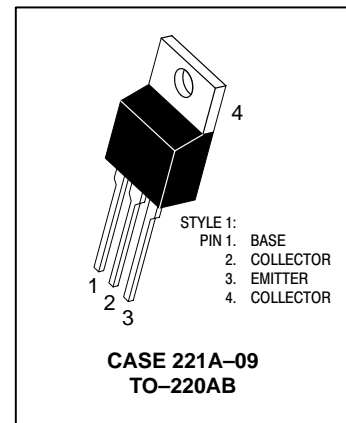
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	70	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	70	$^\circ\text{C/W}$

NPN
BDX53B

BDX53C
PNP
BDX54B

BDX54C

DARLINGTON
8 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
80-100 VOLTS
65 WATTS



BDX53B BDX53C BDX54B BDX54C

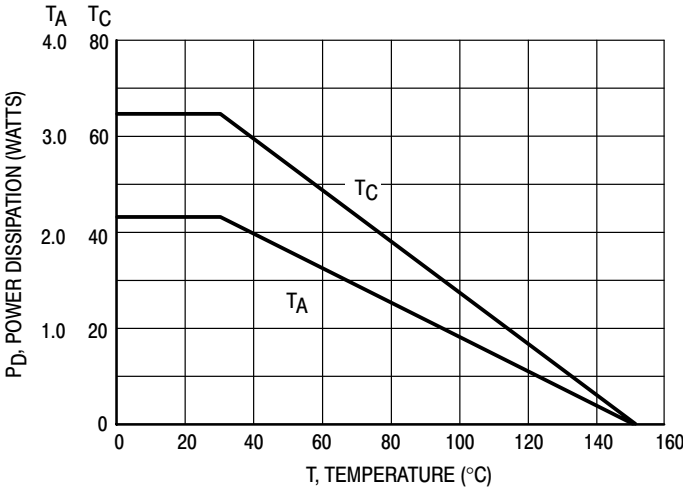


Figure 1. Power Derating

BDX53B BDX53C BDX54B BDX54C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) ($I_C = 100\text{ mAdc}$, $I_B = 0$)	BDX53B, BDX54B BDX53C, BDX54C	$V_{CE(sus)}$	80 100	— —	Vdc
Collector Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 50\text{ Vdc}$, $I_B = 0$)	BDX53B, BDX54B BDX53C, BDX54C	I_{CEO}	— —	0.5 0.5	mAdc
Collector Cutoff Current ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$)	BDX53B, BDX54B BDX53C, BDX54C	I_{CBO}	— —	0.2 0.2	mAdc
ON CHARACTERISTICS (1)					
DC Current Gain ($I_C = 3.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)		h_{FE}	750	—	—
Collector–Emitter Saturation Voltage ($I_C = 3.0\text{ Adc}$, $I_B = 12\text{ mAdc}$)		$V_{CE(sat)}$	— —	2.0 4.0	Vdc
Base–Emitter Saturation Voltage ($I_C = 3.0\text{ Adc}$, $I_C = 12\text{ mA}$)		$V_{BE(sat)}$	—	2.5	Vdc
DYNAMIC CHARACTERISTICS					
Small–Signal Current Gain ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)		h_{fe}	4.0	—	—
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 0.1\text{ MHz}$)	BDX53B, 53C BDX54B, 54C	C_{ob}	— —	300 200	pF

(1) Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

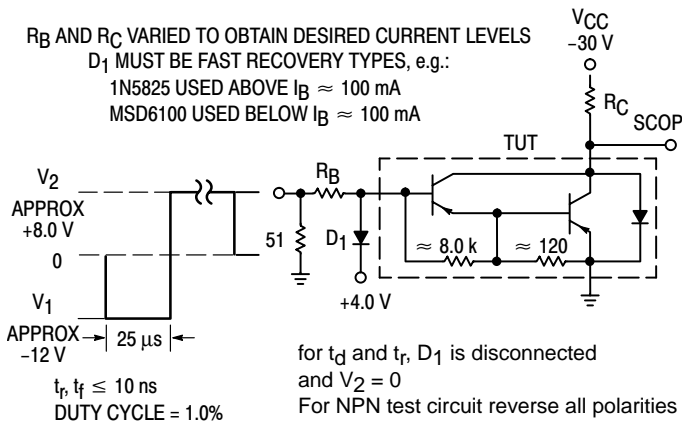


Figure 2. Switching Time Test Circuit

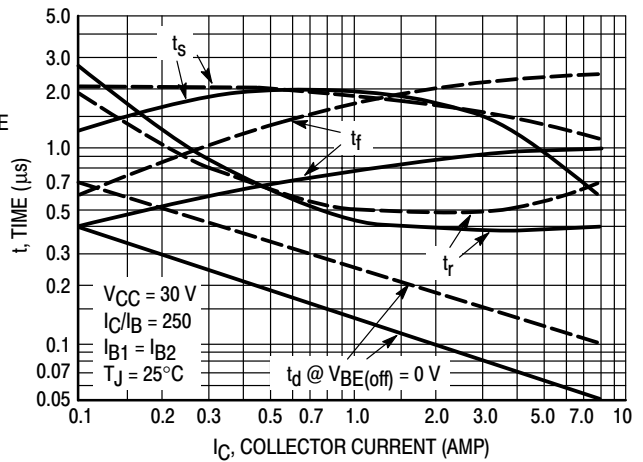


Figure 3. Switching Times

BDX53B BDX53C BDX54B BDX54C

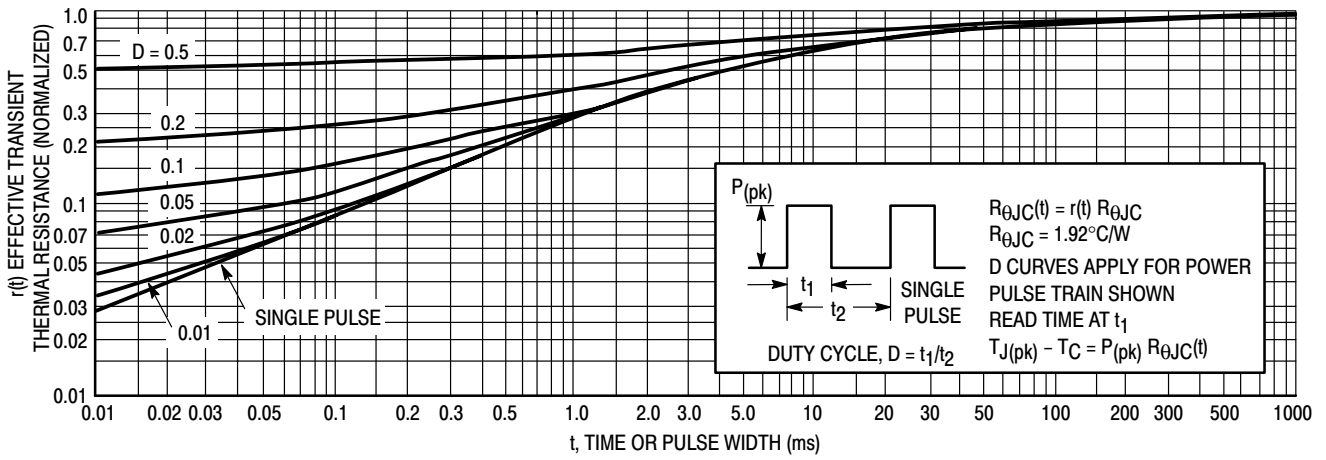


Figure 4. Thermal Response

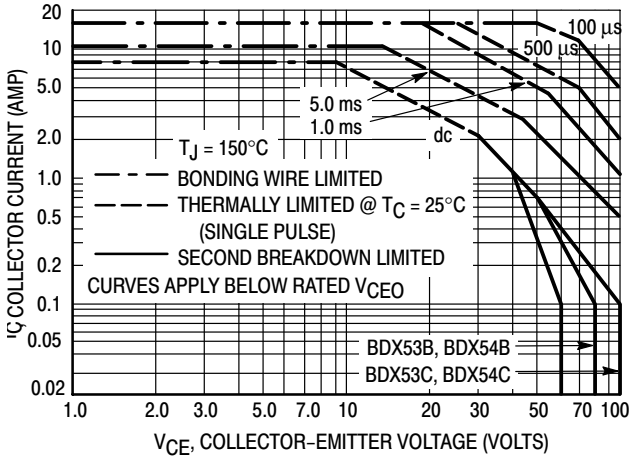


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_J(pk) = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_J(pk) < 150^\circ\text{C}$. $T_J(pk)$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

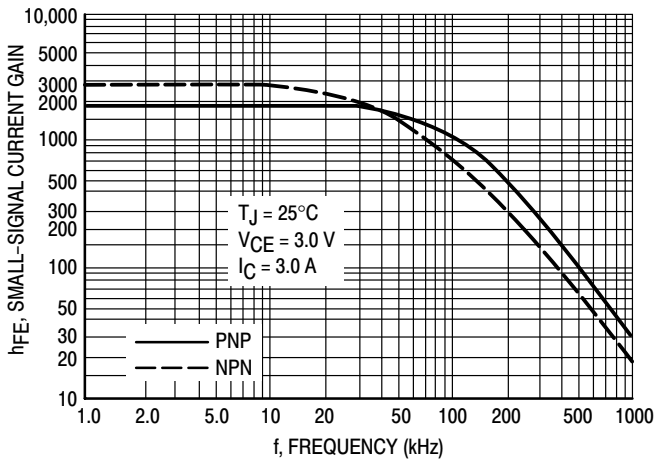


Figure 6. Small-Signal Current Gain

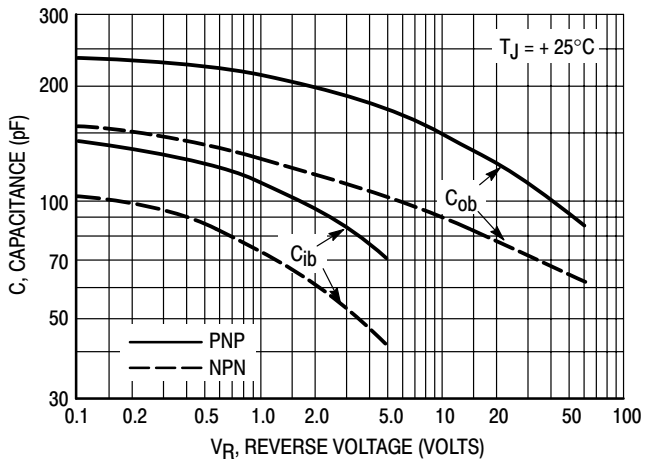


Figure 7. Capacitance

BDX53B BDX53C BDX54B BDX54C

NPN
BDX53B, 53C

PNP
BDX54B, 54C

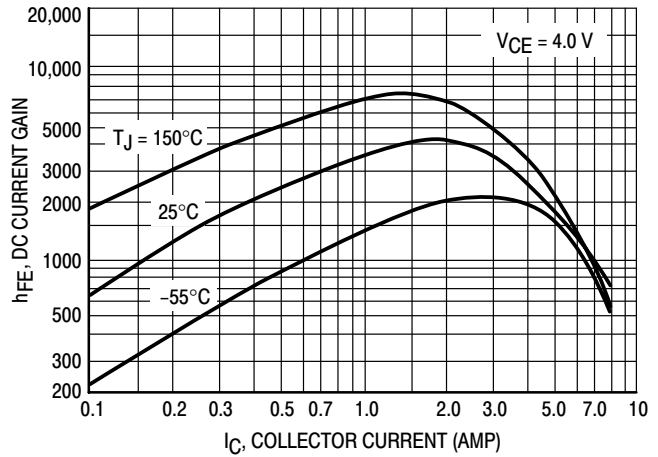
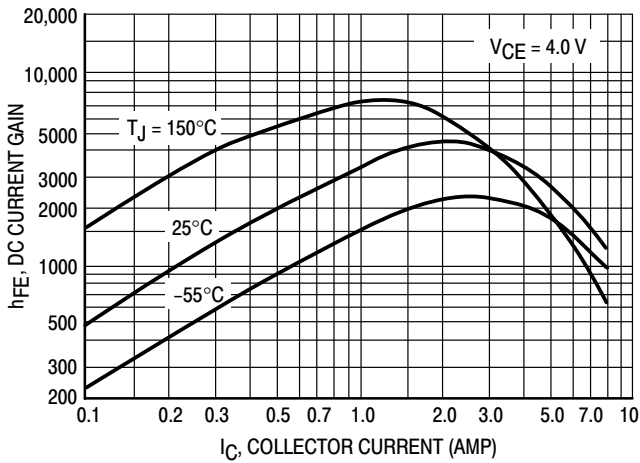


Figure 8. DC Current Gain

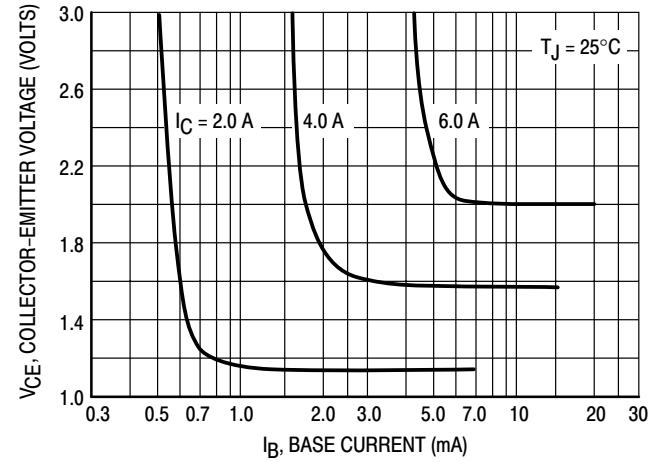
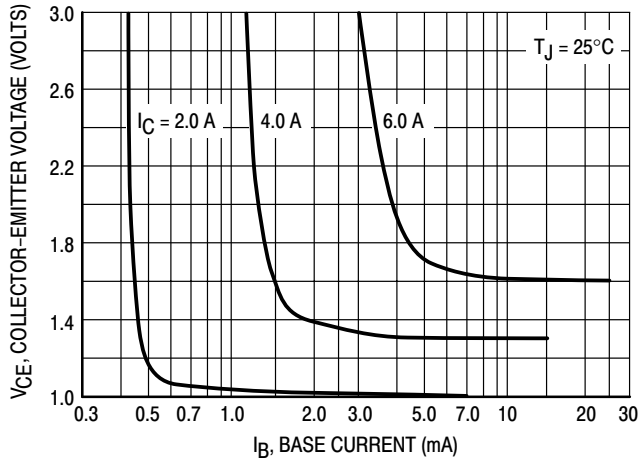


Figure 9. Collector Saturation Region

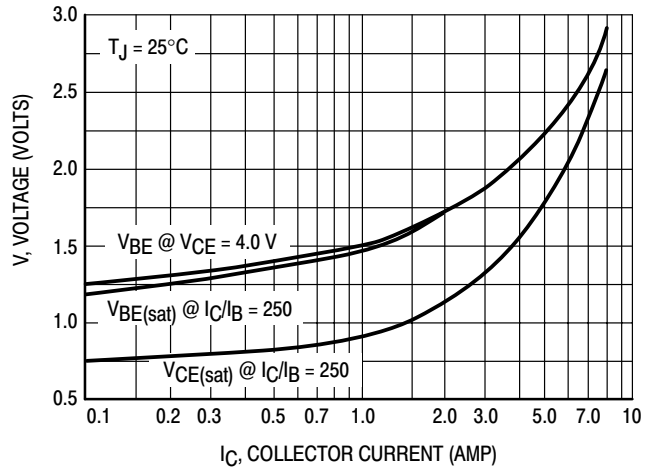
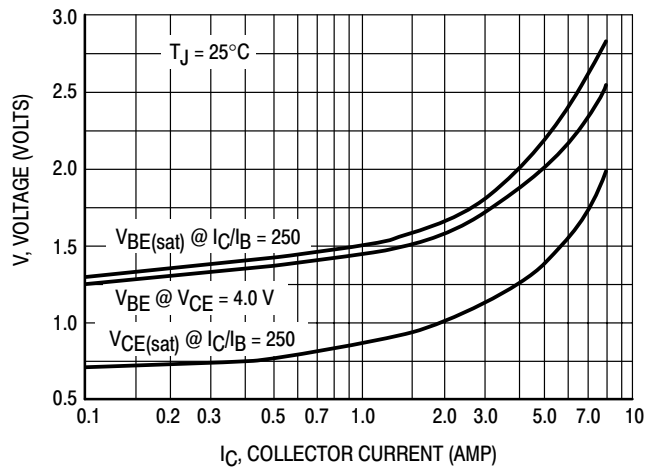


Figure 10. "On" Voltages

BDX53B BDX53C BDX54B BDX54C

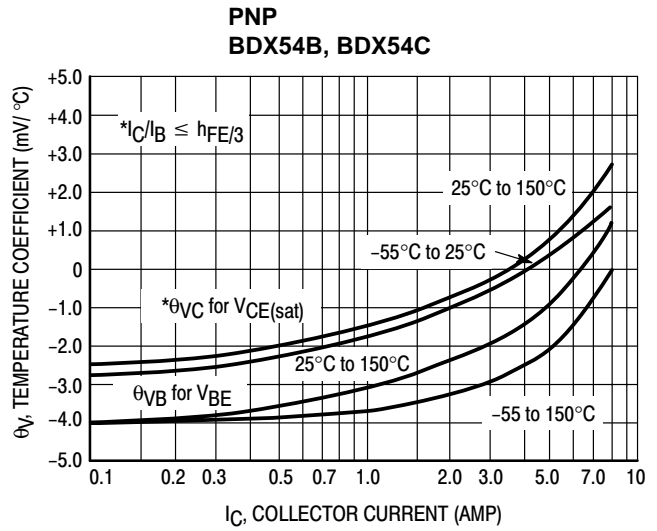
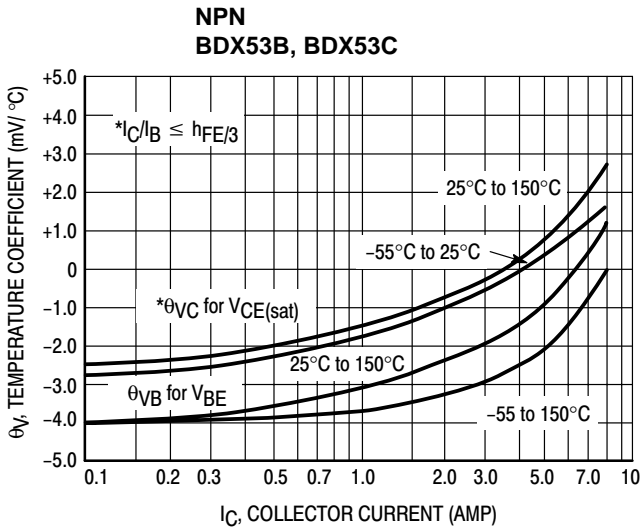


Figure 11. Temperature Coefficients

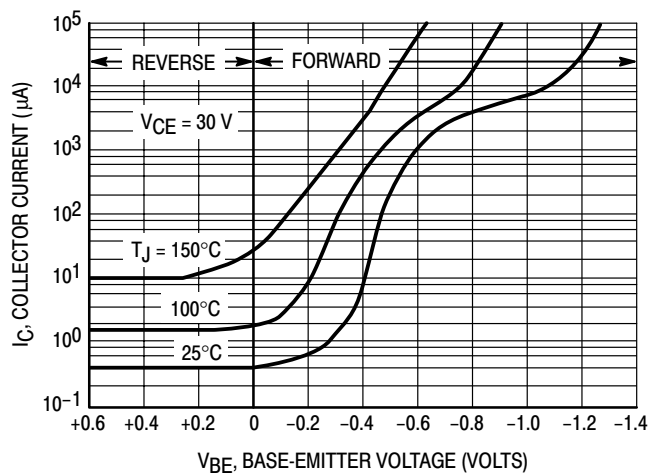
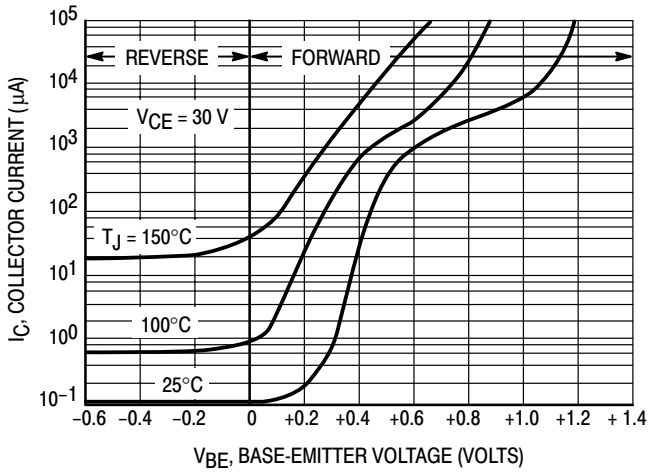


Figure 12. Collector Cut-Off Region

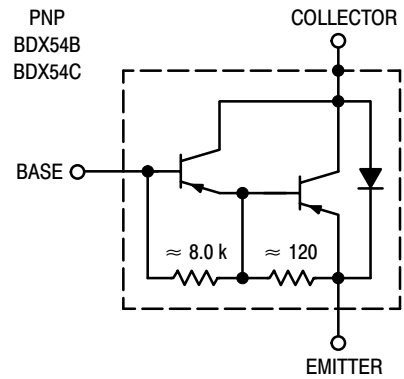
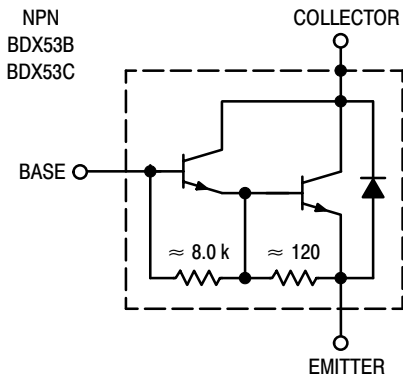
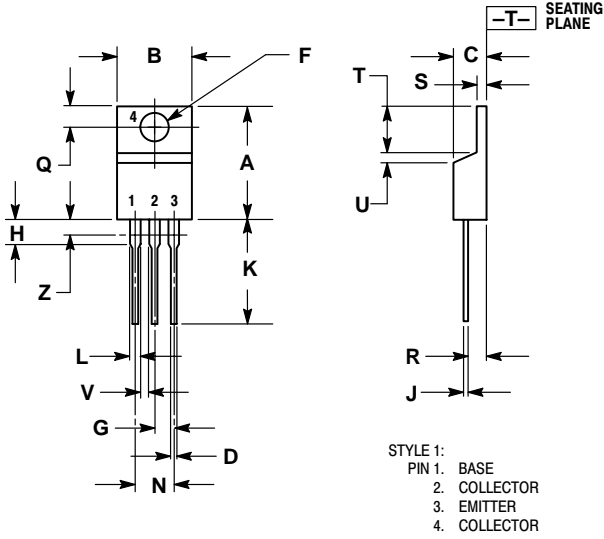


Figure 13. Darlington Schematic

BDX53B BDX53C BDX54B BDX54C

PACKAGE DIMENSIONS

TO-220AB
CASE 221A-09
ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

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